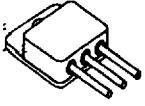


NEW ENGLAND SEMICONDUCTOR

POWER MOSFETS

N CHANNEL

TO-258

PACKAGE	DEVICE TYPE	BV _{DSS} VOLTS	I _D AMPS	R _{DS(on)} @0.5 I _D OHMS	Q _g nc	C _{iss} pf	P _D WATTS
	NSF41013	1000	9.0	1.3	90	2950	250
	NSF41011	1000	12.0	1.1	122	4200	250
	NSF40913	900	9.0	1.3	90	2950	250
	NSF40911	900	12.0	1.1	123	4200	250
	NSG40809	800	10.5	0.90	88	2950	250
	NSF40808	800	13.0	0.80	130	4200	250
	NSF40709	700	10.5	0.90	88	2950	250
	NSF40708	700	11.5	0.80	88	2950	250
	NSF406045	600	15.5	0.45	88	2950	250
	NSF40604	600	20.0	0.40	150	4200	250
	NSF40505	500	21.0	0.25	83	2950	250
	NSF40504	500	19.0	0.30	83	2950	250
	NSF405023	500	24.0	0.23	130	4200	250
	NSF40402	400	23.0	0.20	94	2950	250
	NSF404025	400	20.0	0.25	94	2950	250
	NSF403009	300	40.0	0.09	200	4500	250
	NSF402005	200	50.0	0.05	220	4500	250
	NSF401002	100	75.0	0.025	230	4500	250

- Electrical Characteristics @ 25° C unless otherwise noted
- Operational Temperature range: -55° to +150° C
- Storage temperature range: -55° to +150° C